

New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

OPTO ELECTRONICS DETECTORS—PROGRAMMABLE UNIUNCTION TRANSISTORS

GE Type	Anode-Cathode Voltage Max. (V)	D.C. Anode Current Max. (mA)	Rise Time Typical (nsec)	Irradiance to Trigger @ $R_g=800k\Omega$, $V_s=10V$ Max.	Forward on Voltage V_f Max. (V)	P_f Max. (mW)	Package Type	Package Outline No.	Specification Sheet No.
L14T	± 40	100	80	1mW/Cm ²	1.5	200	T0-92	263	55,54

OPTO ELECTRONICS DETECTORS—SCSs

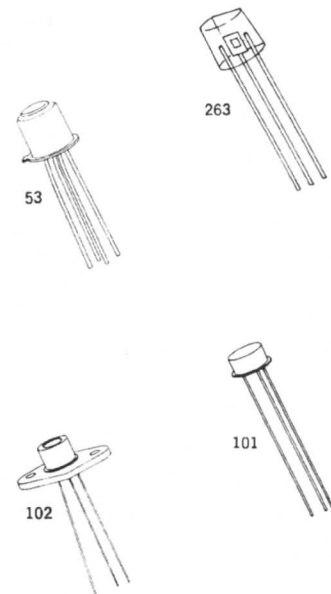
GE Type	Voltage Anode to Cathode Forward and Reverse Max. (V)	Forward Voltage at 175ma Anode Current @ $R_g = 27k\Omega$ Max. (V)	Holding Current @ $R_{th} = 27k\Omega$ Max. (mA)	Cathode Gate Current to Fire @ $V_{AC} = 40V$, $R_A = 800\Omega$ Max. (μA)	Effective Irradiance To Trigger @ $V_{AC} = 40V$, $R_A = 800\Omega$ Max.	Package Type	Package Outline No.	Specification Sheet No.
L1V	40	2.3	2.0	10	10mW/Cm ²	T0-18	53	55.41

OPTO ELECTRONICS DETECTORS—SCR's

GE Type	PRV/V _{BO}	I _{bc} @ 25°C Max. (A)	Max. Temp. °C		Effective Irradiance (mw/cm ²) to Trigger ¹ at 25°C T _J , 6Vdc		Package Outline No.	Specification Sheet No.
			Oper.	Stor.	Min.	Max.		
L8U	25	.44	100°	150°	0.68	10.0	101	190.10
L8F	50	.44	100°	150°	0.68	10.0	101	190.10
L8A	100	.44	100°	150°	0.68	10.0	101	190.10
L8B	150	.44	100°	150°	0.68	10.0	101	190.10
L8G	200	.44	100°	150°	0.68	10.0	101	190.10
L811U	25	.77	100°	150°	0.68	10.0	102	190.10
L811F	50	.77	100°	150°	0.68	10.0	102	190.10
L811A	100	.77	100°	150°	0.68	10.0	102	190.10
L811B	150	.77	100°	150°	0.68	10.0	102	190.10
L811G	200	.77	100°	150°	0.68	10.0	102	190.10
L9U	25	.44	100°	150°	0.68	4.2	101	190.10
L9F	50	.44	100°	150°	0.68	4.2	101	190.10
L9A	100	.44	100°	150°	0.68	4.2	101	190.10
L9B	150	.44	100°	150°	0.68	4.2	101	190.10
L9G	200	.44	100°	150°	0.68	4.2	101	190.10
L911U	25	.77	100°	150°	0.68	4.2	102	190.10
L911F	50	.77	100°	150°	0.68	4.2	102	190.10
L911A	100	.77	100°	150°	0.68	4.2	102	190.10
L911B	150	.77	100°	150°	0.68	4.2	102	190.10
L911G	200	.77	100°	150°	0.68	4.2	102	190.10

NOTE: Gate current to trigger from direct electrical supply is 20 μA typical, 200 μA maximum at 25°C T_J.

¹ Effective Irradiance to trigger decreases with increasing anode voltage and increasing gate to cathode resistance.



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors